

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _A = +25°C
-30V	0.9Ω @ V _{GS} = -10V	-0.81 A
	1.7Ω @ V _{GS} = -4.5V	-0.58 A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Load Switch

Features and Benefits

- 0.6mm² Footprint—Thirteen Times Smaller than SOT23
- Low Gate Threshold Voltage
- Fast Switching Speed
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

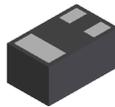
Mechanical Data

- Package: X1-DFN1006-3
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 [e4](#)
- Weight: 0.001 grams (Approximate)

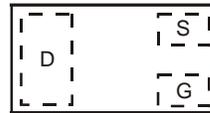


ESD Protected Gate

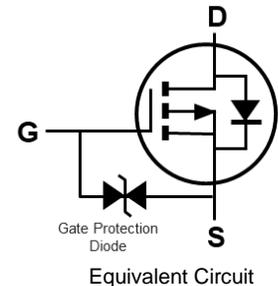
X1-DFN1006-3



Bottom View



Top View
Internal Schematic



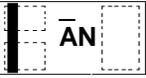
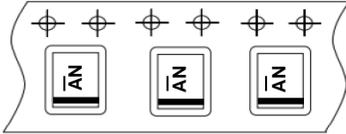
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Package	Marking	Reel Size (inches)	Tape Width (mm)	Tape Pitch (mm)	Packing	
						Qty.	Carrier
DMP31D7LFB-7B	X1-DFN1006-3	AN	7	8	2	10,000	Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3), compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

DMP31D7LFB-7B	 <p>Top View Bar Denotes Gate and Source Side</p>	$\bar{A}N$ = Product Type Marking Code
		

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	± 20	V
Continuous Drain Current (Note 6) $V_{GS} = 4.5\text{V}$	Steady State	$T_A = +25^\circ\text{C}$	I_D	-0.81	A
		$T_A = +70^\circ\text{C}$		-0.64	A
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)			I_{DM}	-2.4	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	0.53	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	236	$^\circ\text{C/W}$
Total Power Dissipation (Note 6)	P_D	0.89	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	141	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 25mm x 25mm square copper plate.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	-1	μA	V _{DS} = -24V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±16V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-1	—	-2.6	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	0.5	0.9	Ω	V _{GS} = -10V, I _D = -0.42A
		—	0.8	1.7		V _{GS} = -4.5V, I _D = -0.2A
Diode Forward Voltage	V _{SD}	—	-0.8	-1.2	V	V _{GS} = 0V, I _S = -0.23A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	19	—	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	16	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	3	—	pF	V _{DS} = V _{GS} = 0V, f = 1.0MHz
Gate Resistance	R _g	—	729	—	Ω	
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	0.36	—	nC	V _{GS} = -4.5V, V _{DS} = -10V, I _D = -250mA
Gate-Source Charge	Q _{gs}	—	0.1	—	nC	
Gate-Drain Charge	Q _{gd}	—	0.1	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	30	—	ns	V _{DD} = -10V, V _{GS} = -4.5V, R _L = 47Ω, R _G = 10Ω, I _D = -200mA
Turn-On Rise Time	t _R	—	74	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	28	—	ns	
Turn-Off Fall Time	t _F	—	31	—	ns	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

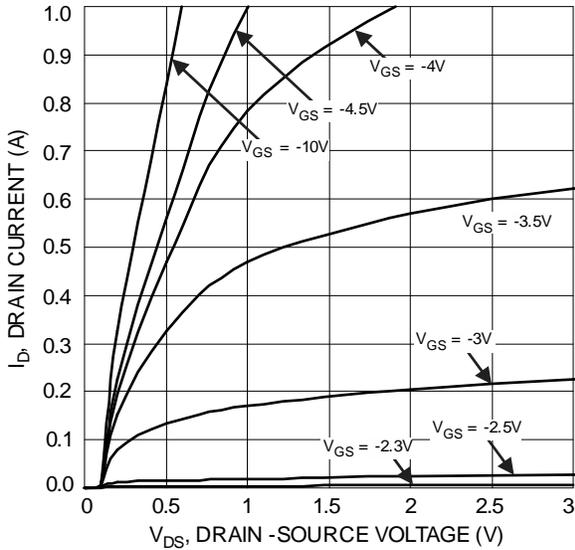


Figure 1 Typical Output Characteristics

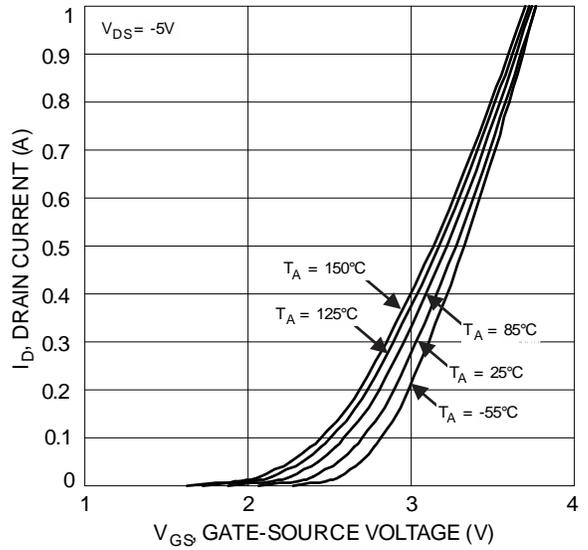


Figure 2 Typical Transfer Characteristics

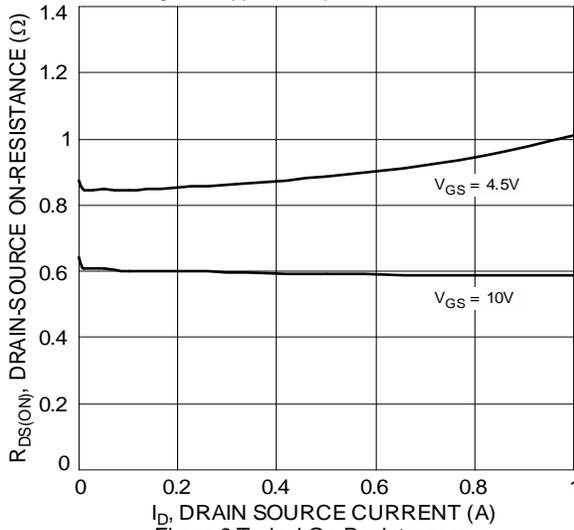


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

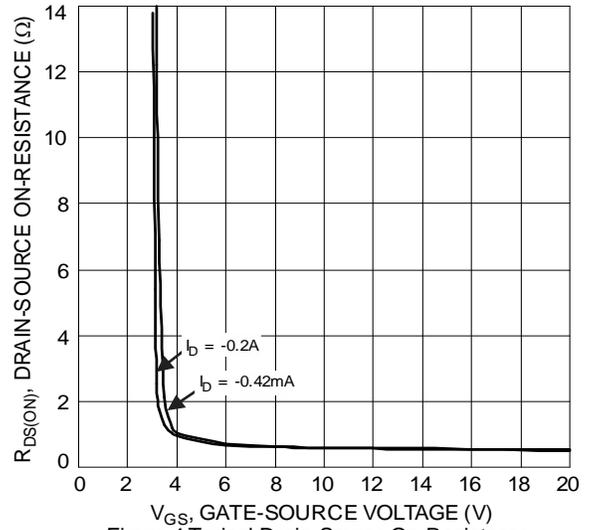


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

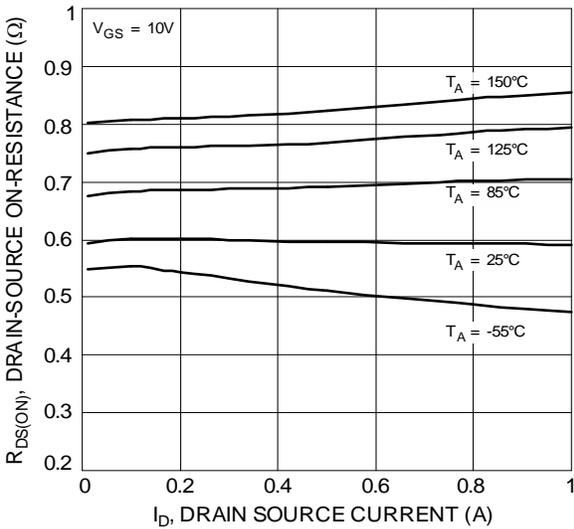


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

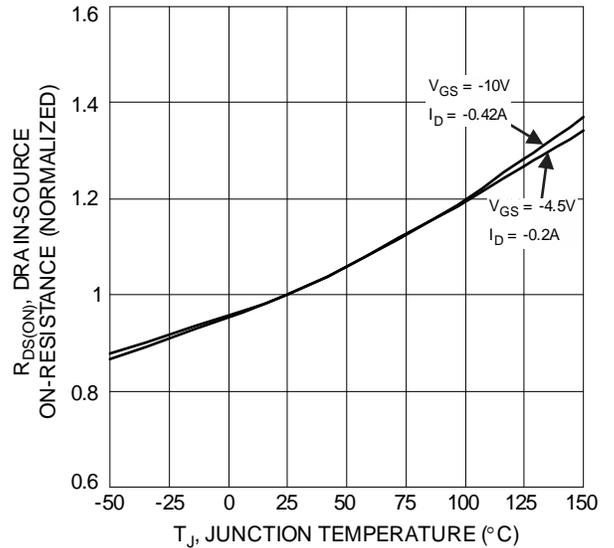


Figure 6 On-Resistance Variation with Temperature

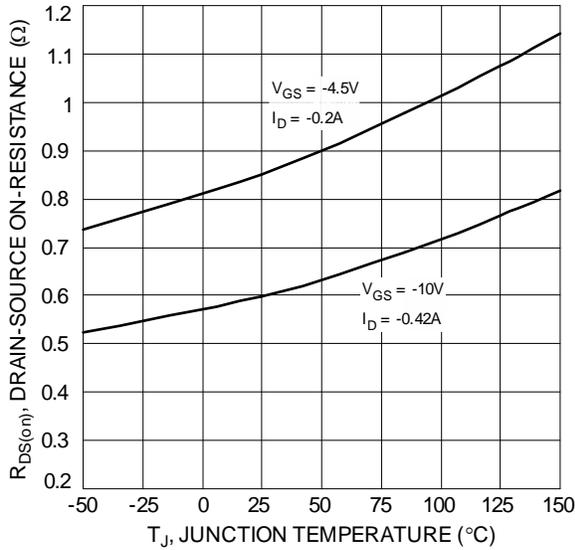


Figure 7 On-Resistance Variation with Temperature

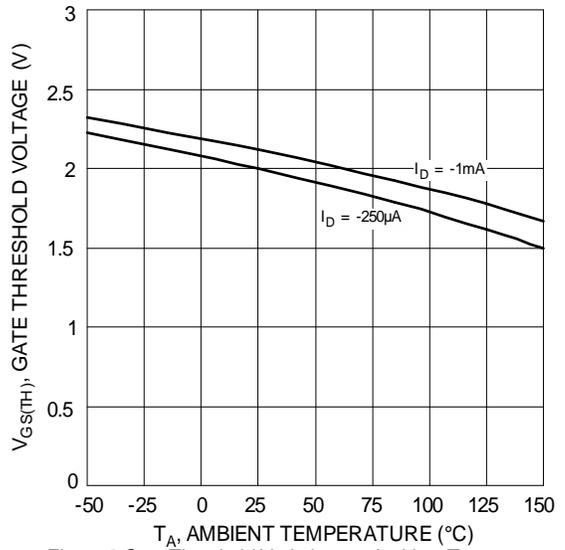


Figure 8 Gate Threshold Variation vs. Ambient Temperature

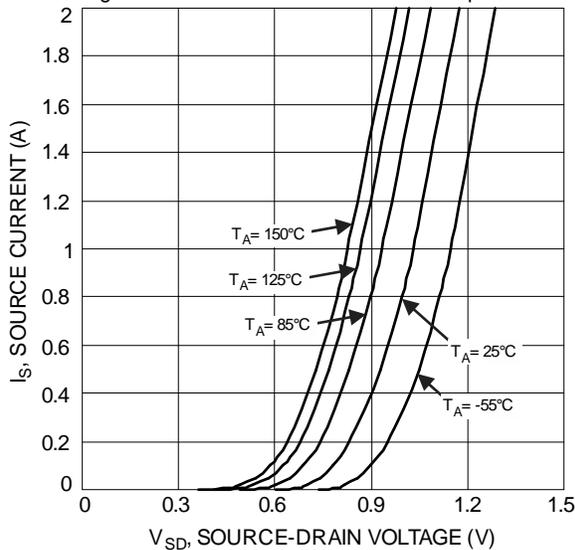


Figure 9 Diode Forward Voltage vs. Current

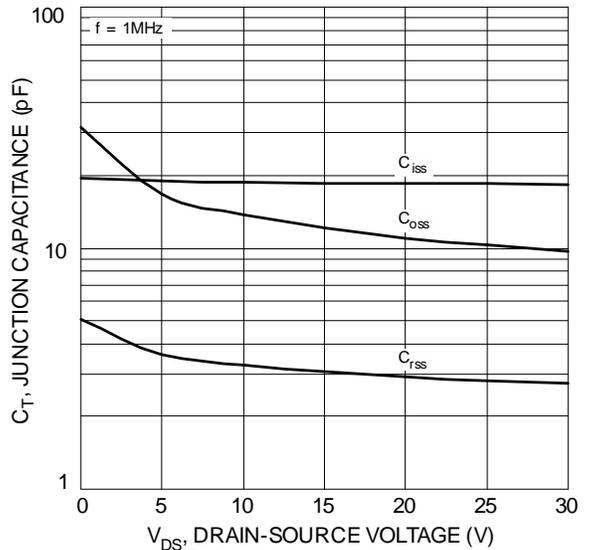


Figure 10 Typical Junction Capacitance

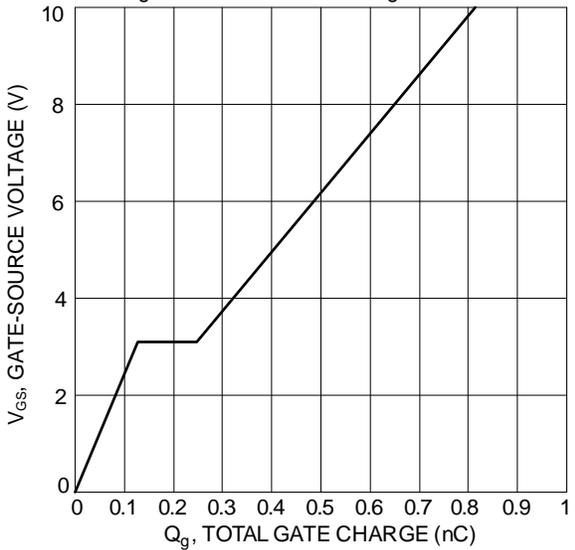


Figure 11 Gate Charge

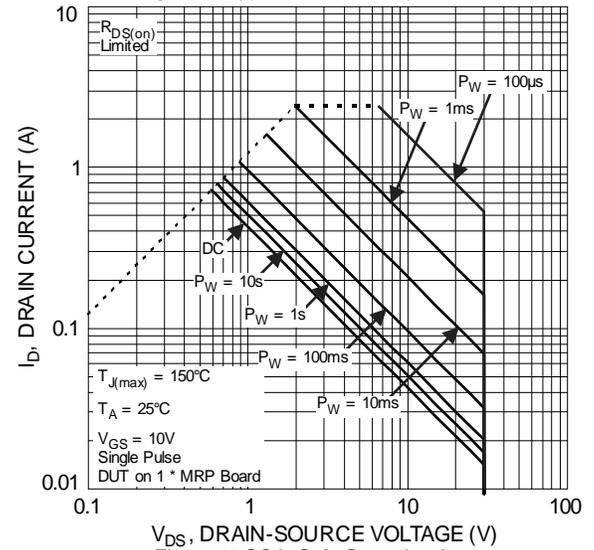
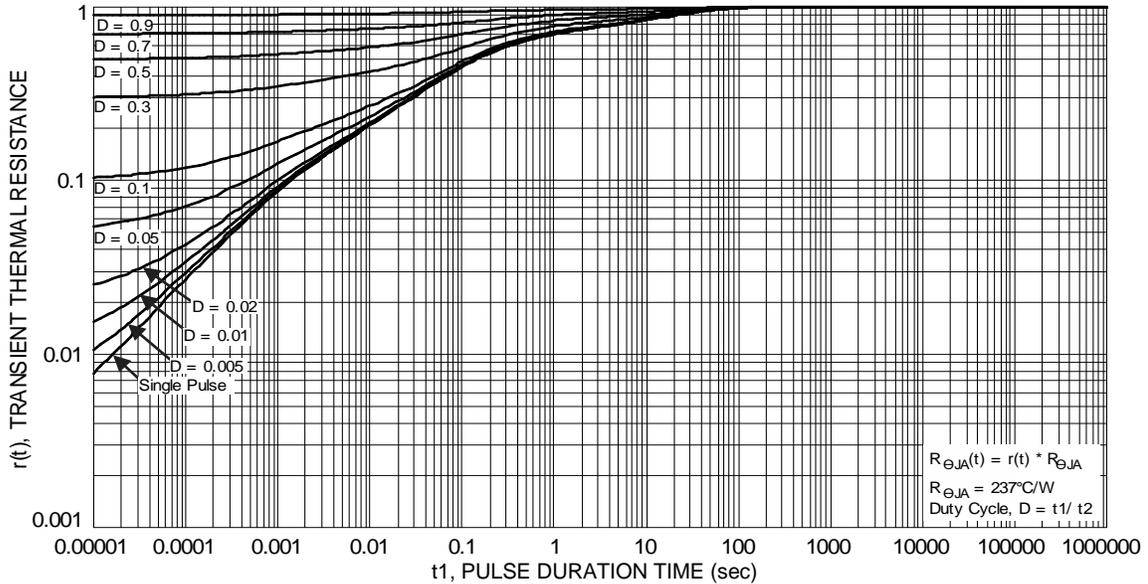


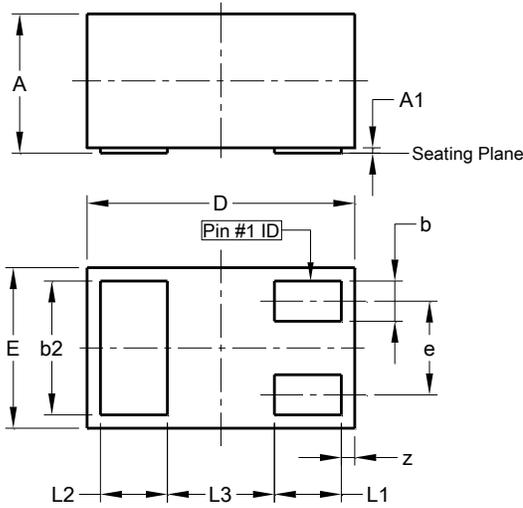
Figure 12 SOA, Safe Operation Area



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X1-DFN1006-3

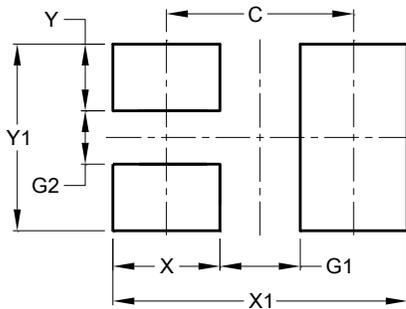


X1-DFN1006-3			
Dim	Min	Max	Typ
A	0.47	0.53	0.50
A1	0.00	0.05	0.03
b	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	-	-	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	-	-	0.40
z	0.02	0.08	0.05
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X1-DFN1006-3



Dimensions	Value (in mm)
C	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Y	0.25
Y1	0.70

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